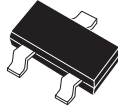


CMPT5551

NPN SILICON TRANSISTOR



SOT-23 CASE

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPT5551 type is an NPN silicon transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for high voltage amplifier applications.

Marking Code is 1FF.

MAXIMUM RATINGS (T_A=25°C)

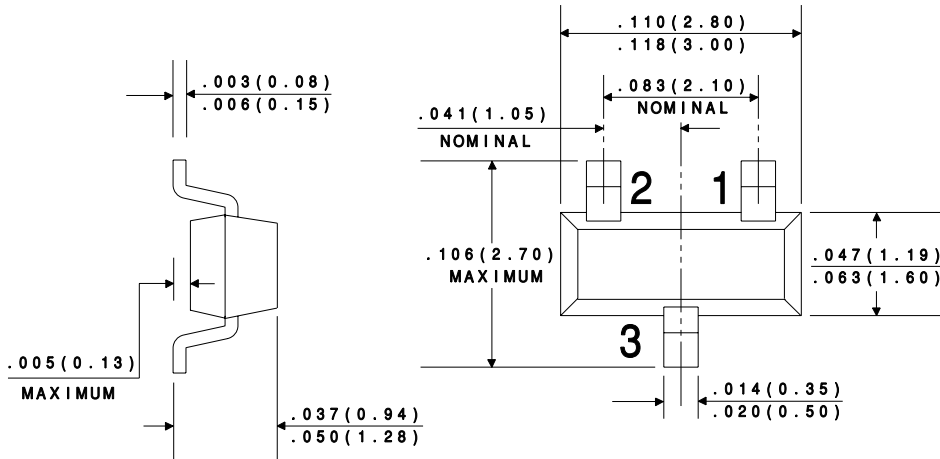
	SYMBOL		UNITS
Collector-Base Voltage	V _{CB0}	180	V
Collector-Emitter Voltage	V _{CEO}	160	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current	I _C	600	mA
Power Dissipation	P _D	350	mW
Operating and Storage			
Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance	θ _{JA}	357	°C/W

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I _{CB0}	V _{CB} =120V		50	nA
I _{CB0}	V _{CB} =120V, T _A =100°C		50	μA
BV _{CB0}	I _C =100μA	180		V
BV _{CEO}	I _C =1.0mA	160		V
BV _{EBO}	I _E =10μA	6.0		V
V _{CE(SAT)}	I _C =10mA, I _B =1.0mA		0.15	V
V _{CE(SAT)}	I _C =50mA, I _B =5.0mA		0.20	V
V _{BE(SAT)}	I _C =10mA, I _B =1.0mA		1.00	V
V _{BE(SAT)}	I _C =50mA, I _B =5.0mA		1.00	V
h _{FE}	V _{CE} =5.0V, I _C =1.0mA	80		
h _{FE}	V _{CE} =5.0V, I _C =10mA	80	250	
h _{FE}	V _{CE} =5.0V, I _C =50mA	30		
f _T	V _{CE} =10V, I _C =10mA, f=100MHz	100	300	MHz
C _{ob}	V _{CB} =10V, I _E =0, f=1.0MHz		6.0	pF

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
h_{fe}	$V_{CE}=10V, I_C=1.0mA, f=1.0kHz$	50	200	
N_F	$V_{CE}=5.0V, I_C=200\mu A, R_S=10\Omega$ $f=10Hz$ to $15.7kHz$		8.0	dB

All dimensions in inches (mm).



LEAD CODE:

- 1) BASE
- 2) EMITTER
- 3) COLLECTOR